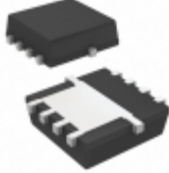

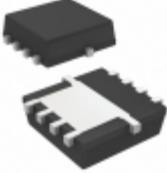
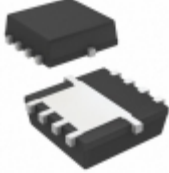
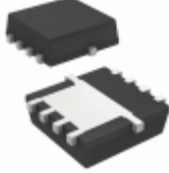
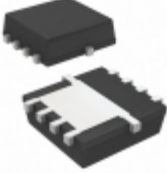

	<h2>SI7820DN-T1-E3</h2>
	<p>Hersteller-Teilenummer: SI7820DN-T1-E3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET N-CH 200V 1.7A 1212-8</p> <p>Datenblätter:  SI7820DN-T1-E3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 7370 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI7820DN-T1-E3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET N-CH 200V 1.7A 1212-8
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	7370 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	PowerPAK® 1212-8
Supplier Device-Gehäuse	PowerPAK® 1212-8
Verlustleistung (max)	1.5W (Ta)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	200V
Strom - Ununterbrochener Abfluss (Id) bei 25 °C	1.7A (Ta)
Rds On (Max) @ Id, Vgs	240 mOhm @ 2.6A, 10V
VGS (th) (Max) @ Id	4V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	18nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	-
Antriebsspannung (Max Rds On, Min Rds On)	6V, 10V
Vgs (Max)	±20V
Verpackung	Tape & Reel (TR)

SI7820DN-T1-E3 ist neu im Original, Suche SI7820DN-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7820DN-T1-E3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI7820DN-T1-E3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI7820DN-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 200V 1.7A 1212-8</p>	 <p>SI7840 SI SI7840 SI</p>	 <p>SI7820DN-T1-GE3 Vishay / Siliconix MOSFET N-CH 200V 1.7A 1212-8</p>	 <p>SI7818DN-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 150V 2.2A 1212-8</p>
 <p>SI7820DN-T1-E3 Electro-Films (EFI) / Vishay MOSFET N-CH 200V 1.7A 1212-8</p>	 <p>SI7818DN-T1-GE3 Vishay / Siliconix MOSFET N-CH 150V 2.2A 1212-8</p>	 <p>SI7818DN-T1-E3 Electro-Films (EFI) / Vishay MOSFET N-CH 150V 2.2A 1212-8</p>	 <p>SI7840BDP-T1-E3 Vishay / Siliconix MOSFET N-CH 30V 11A PPAK SO-8</p>

heiße Teile

Mehr

 SI7804DN-T1-E3	 SI7804DN-T1-E3	 SI7806ADN	 SI7806ADN-T1-E3	 SI7806ADN-T1-E3
 SI7806ADN-T1-E3-PBF	 SI7806ADN-T1-GE3	 SI7806ADN-T1-GE3	 SI7806AEDN-T1-E3	 SI7806BDN
 SI7806BDN-T1-GE3	 SI7806DN-T1-E3	 SI7806DN-T1-GE3	 SI7810DN	 SI7810DN-T1
 SI7810DN-T1-E	 SI7810DN-T1-E3	 SI7810DN-T1-E3	 SI7812DN-T1-E3	 SI7812DN-T1-E3
 SI7812DN-T1-GE3	 SI7812DN-T1-GE3	 SI7818DN-T1-E3	 SI7818DN-T1-E3	 SI7820DN-T1-E3
 SI7820DN-T1-GE3	 SI7820DN-T1-GE3	 SI7840BDP	 SI7840BDP-T1-E3	 SI7840BDP-T1-E3
 SI7840BDP-T1-GE3	 SI7840BDP-T1-GE3	 SI7840DP	 SI7840DP-T1	 SI7840DP-T1-E3
 SI7840DP-T1-GE3	 SI7840DP-T1-GE3	 SI7842DP	 SI7842DP-T1-E3	 SI7842DP-T1-E3
 SI7842DP-T1-GE3	 SI7842DP-T1-GE3	 SI7844DP	 SI7844DP-T1	 SI7844DP-T1-E3
 SI7844DP-T1-E3	 SI7844DP-T1-GE3	 SI7844DP-T1-GE3	 SI7846DP	 SI7846DP-T1-E3

Contact us: Info@Y-IC.com

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